

Practitioner's Docket No.: 811\_107

**AFTER FINAL  
PATENT**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re the Application of: Makoto IWAI, Katsuhiro IMAI and Minoru IMAEDA

Serial No.: 10/594,846

Group Art Unit: 1714

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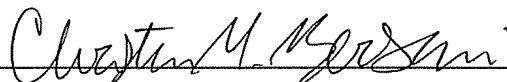
Conf. No.: 3664

For: GALLIUM NITRIDE SINGLE CRYSTAL GROWING METHOD  
AND GALLIUM NITRIDE SINGLE CRYSTAL

Mail Stop RCE  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**CERTIFICATION OF EFS  
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I hereby certify that this paper is being transmitted via EFS to the Patent and Trademark Office on October 22, 2010.

  
Christina M. Bersani

**AMENDMENT AFTER FINAL REJECTION\***

Sir:

In response to the Office Action mailed July 22, 2010, please amend the above-identified application as follows:

**Amendments to the Claims** begin on page 2 of this paper.

**Remarks/Arguments** begin on page 4 of this paper.

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\* An RCE is filed herewith.